



#### **DUAL 30V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON) max</sub>	I <sub>D max</sub> T <sub>A</sub> = +25°C
001/	$50m\Omega$ @ $V_{GS} = 10V$	4.0A
30V	90mΩ @ V <sub>GS</sub> = 4.5V	3.3A

#### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power Management Functions

#### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)

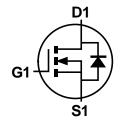
#### TSOT26

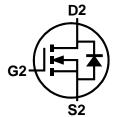


Top View



S2 2





**Equivalent Circuit** 

### **Ordering Information (Note 4)**

Part Number	Case	Packaging
DMN3071LVT-7	TSOT26	3000 / Tape & Reel
DMN3071LVT-13	TSOT26	10,000 / Tape & Reel

6 D1

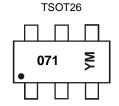
5 S1

4 D2

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



071 = Product Type Marking Code YM or  $\overline{Y}$ M = Date Code Marking Y or  $\overline{Y}$  = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2018	201	9	2020	2021	202	22	2023	2024	20	25	2026
Code	F	G		Н	ı	J		K	L	N	M	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	30	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	I <sub>D</sub>	4.0 3.3	А	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	1.5	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle =	: 1%)	I <sub>DM</sub>	20	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_{D}$	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>OJA</sub>	185	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>OJA</sub>	116	°C/W
Operating and Storage Temperature Range	·	$T_{J_i}T_{STG}$	-55 to +150	°C

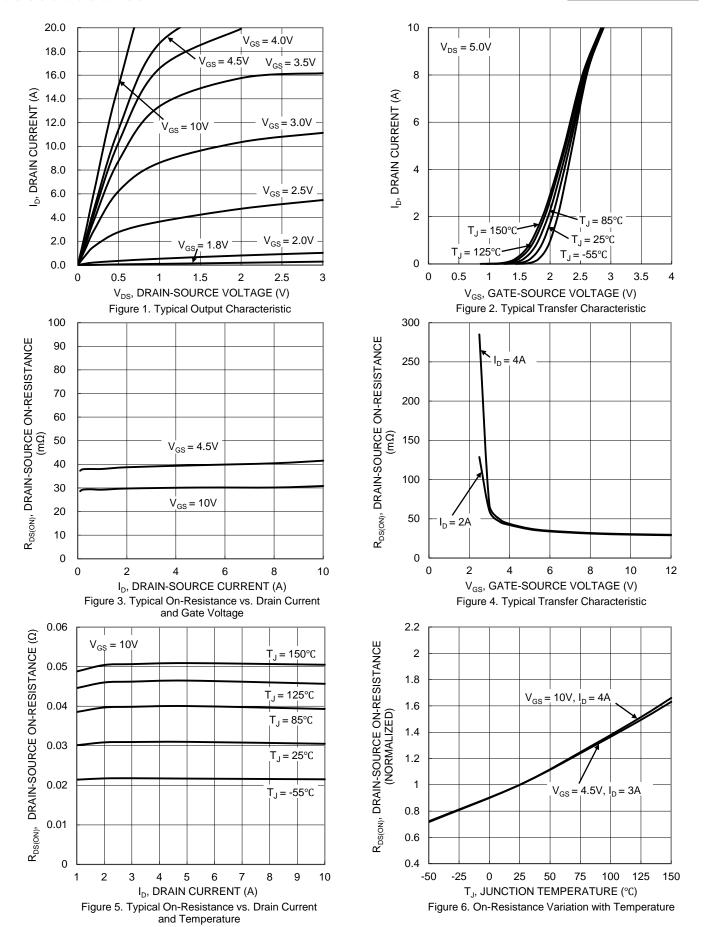
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
	OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$			
Zero Gate Voltage Drain Current $T_J = +25$ °C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$			
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			
Static Drain-Source On-Resistance	В		35	50	mΩ	$V_{GS} = 10V, I_D = 3.5A$			
Static Dialii-Source Oil-Resistance	R <sub>DS(ON)</sub>		48	90	11122	$V_{GS} = 4.5V, I_D = 2A$			
Diode Forward Voltage	$V_{SD}$	ı	0.8	1.0	V	$V_{GS} = 0V, I_{S} = 1.0A$			
DYNAMIC CHARACTERISTICS (Note 8)	DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	ı	190		pF	V 45V V 0V			
Output Capacitance	Coss		36	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ - f = 1.0MHz			
Reverse Transfer Capacitance	Crss	_	26	_	pF	1 = 1.01/1112			
Gate Resistance	$R_g$	ı	4.2		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{g}$		2.1	_	nC				
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	ı	4.5		nC	Vns = 15V. In = 3.5A			
Gate-Source Charge	$Q_{gs}$		0.5		nC	VDS = 15V, ID = 3.5A			
Gate-Drain Charge	$Q_{gd}$	_	0.8	_	nC				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	1.7	_	ns				
Turn-On Rise Time	t <sub>R</sub>	_	5.7	_	ns	$V_{DS} = 15V, V_{GS} = 10V,$			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	6.0	_	ns	$R_G = 3\Omega$ , $R_L = 4.2\Omega$			
Turn-Off Fall Time	t <sub>F</sub>		1.6	_	ns				
Reverse Recovery Time	t <sub>RR</sub>		4.2	_	ns	I <sub>F</sub> = 3.5A, di/dt = 100A/μs			
Reverse Recovery Charge	Q <sub>RR</sub>		0.5	_	nC	I <sub>F</sub> = 3.5A, di/dt = 100A/μs			

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







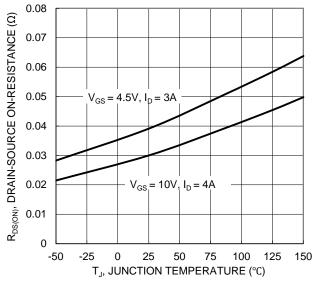


Figure 7. On-Resistance Variation with Temperature

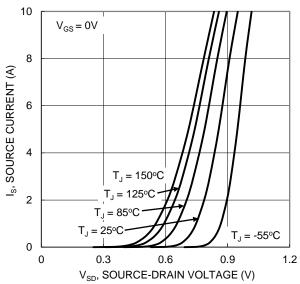


Figure 9. Diode Forward Voltage vs. Current

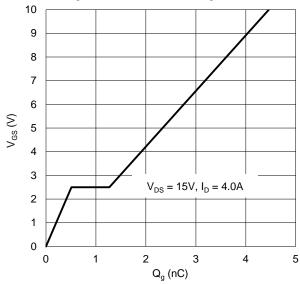


Figure 11. Gate Charge

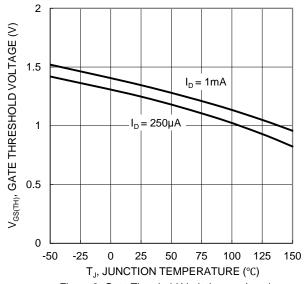
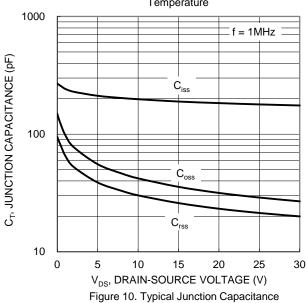


Figure 8. Gate Threshold Variation vs. Junction Temperature



100 R<sub>DS(ON)</sub> = 100µs 10 ID, DRAIN CURRENT (A)  $P_W = 100ms$  $T_{J(Max)} = 150$  °C  $T_C = 25^{\circ}C$ Single Pulse 0.1 DUT on 1\*MRP 10s Board DC  $V_{GS} = 10V$ 0.01 0.1 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



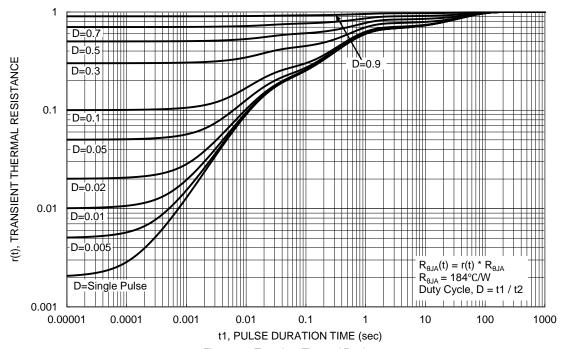
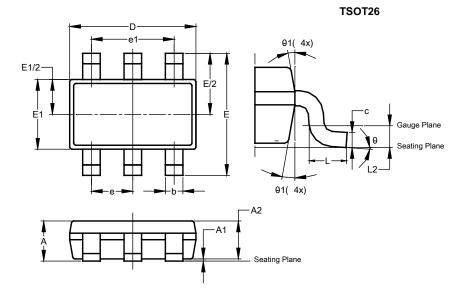


Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

 $\label{prop:package-outlines.html} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

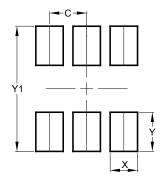


	TSOT26						
Dim	Min	Max	Тур				
Α	1.00						
A1	0.010	0.100					
A2	0.840	0.900					
D	2.800	3.000	2.900				
Е	2	.800 BS	C				
E1	1.500	1.600					
b	0.300	0.450					
С	0.120	0.200					
е	0.950 BSC						
e1	1.900 BSC						
L	0.30	0.50					
L2	0.250 BSC						
θ	0°	8°	4°				
θ1	4° 12° 🗌						
Α	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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